# **CNA1011K** (ON1113)

## Photo Interrupter

For contactless SW and object detection

#### Overview

CNA1011K is a small size photocoupler package consisting of a high efficiency GaAs infrared light emitting diode used as the light emitting element, and a high sensitivity phototransistor is used as the light detecting element.

#### ■ Features

- Highly precise position detection: 0.3 mm
- Wide gap between emitting and detecting elements, suitable for thick plate detection
- Fast response:  $t_r$ ,  $t_f = 6.0 \mu s$  (typ.)
- Small output current variation against change in temperature

### ■ Absolute Maximum Ratings $T_a = 25$ °C

F	Symbol	Rating	Unit	
Input (Light emitting diode)	Power dissipation *1	$P_{\mathrm{D}}$	75	mW
	Forward current	$I_F$	50	mA
	Reverse voltage	V <sub>R</sub>	3	V
Output (Photo transistor)	Collector-emitter voltage (Base open)	V <sub>CEO</sub>	30	V
	Emitter-collector voltage (Base open)	V <sub>ECO</sub>	5	V
	Collector current	$I_{C}$	20	mA
	Collector power dissipation *2	P <sub>C</sub>	100	mW
Operating ambient temperature		T <sub>opr</sub>	-25 to +85	°C
Storage temperature	T <sub>stg</sub>	-30 to +100	°C	

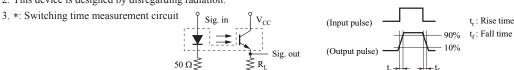
Note) \*1: Input power derating ratio is 1.0 mW/°C at  $T_a \ge 25$ °C

### ■ Electrical-Optical Characteristics $T_a = 25$ °C±3°C

Parameter		Symbol	Conditions	Min	Тур	Max	Unit
Input characteristics	Reverse current	$I_R$	$V_R = 3 V$			10	μА
	Forward voltage	V <sub>F</sub>	$I_F = 50 \text{ mA}$		1.2	1.5	V
	Terminal capacitance	Ct	$V_R = 0 V, f = 1 MHz$		35		pF
Output characteristics	Collector-emitter cutoff current (Base open)	I <sub>CEO</sub>	$V_{\rm CE} = 10 \text{ V}$			200	nA
	Collector-emitter capacitance	C <sub>C</sub>	$V_{CE} = 10 \text{ V, } f = 1 \text{ MHz}$		5		pF
Transfer characteristics	Collector current	$I_{C}$	$V_{CC} = 10 \text{ V}, I_F = 20 \text{ mA},$ $R_L = 100 \Omega$	0.3			mA
	Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_F = 50 \text{ mA}, I_C = 0.1 \text{ mA}$			0.5	V
	Rise time *	t <sub>r</sub>	$V_{CC} = 10 \text{ V}, I_{C} = 1 \text{ mA},$		6.0		μs
	Fall time *	$t_{\mathrm{f}}$	$R_L = 100 \Omega$		6.0		μs

Note) 1. Input and output are practiced by electricity.

2. This device is designed by disregarding radiation.

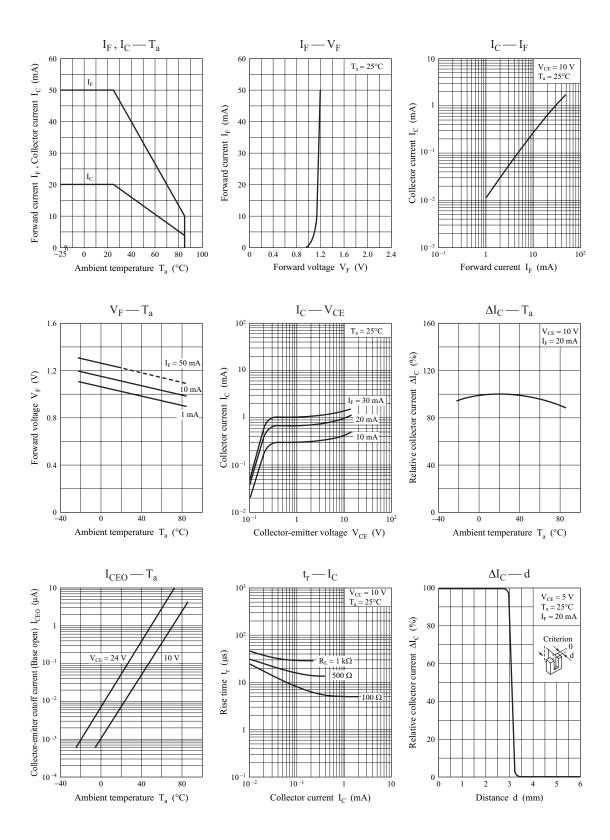


Note) The part number in the parenthesis shows conventional part number.

<sup>\*2:</sup> Output power derating ratio is 1.34 mW/°C at  $T_a \ge 25$ °C

**CNA1011K** 

## **Panasonic**

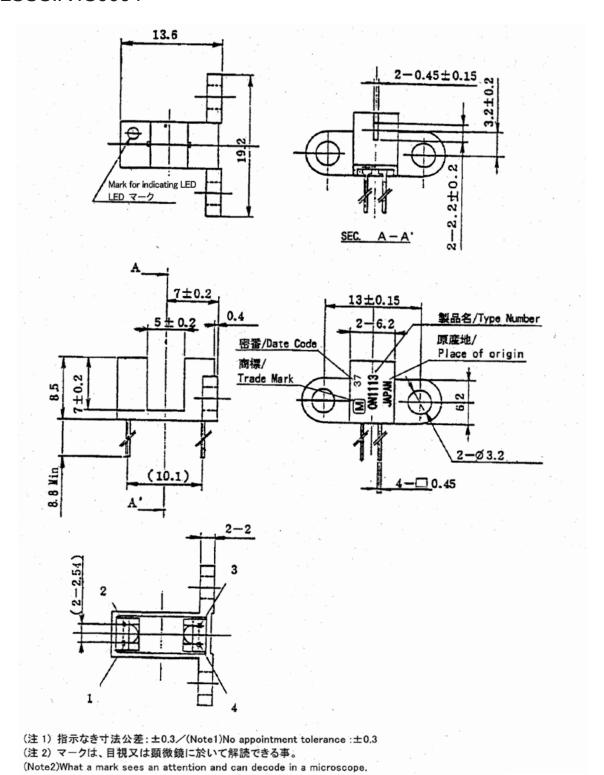


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Panasonic CNA1011K

#### ■ Package (Unit: mm)

## LSSSIR4S0004



- Pin name
  - 1: Anode
  - 2: Cathode
  - 3: Collector
  - 4: Emitter

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